SI4922DY-T1-E3-VB Datasheet

Dual N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
30	0.016 at V_{GS} = 10 V	8.5	7.1
	0.020 at V_{GS} = 4.5 V	7.6	

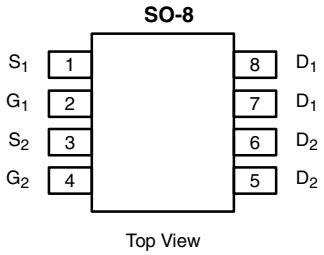
FEATURES

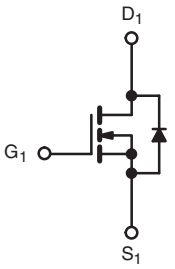
- Trench Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT

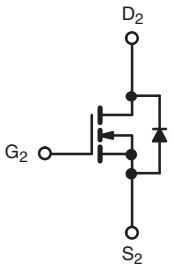
APPLICATIONS

- Notebook System Power
- Low Current DC/DC





N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	8.5	A
	T_C = 70 °C		7.5	
	T_A = 25 °C		7.2[b, c]	
	T_A = 70 °C		5.9[b, c]	
Pulsed Drain Current		I_{DM}	30	
Source-Drain Current Diode Current	T_C = 25 °C	I_S	2.8	
	T_A = 25 °C		1.8[b, c]	
Pulsed Source-Drain Current		I_{SM}	30	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	10	
Single Pulse Avalanche Energy		E_{AS}	5	
Maximum Power Dissipation	T_C = 25 °C	P_D	3.1	W
	T_C = 70 °C		2.0	
	T_A = 25 °C		2.0[b, c]	
	T_A = 70 °C		1.25[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

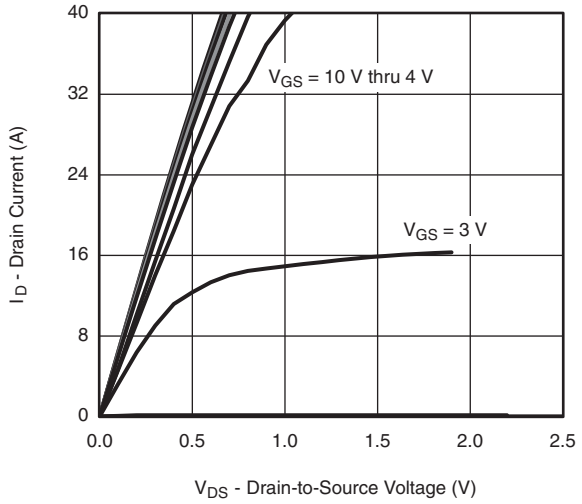
THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typ.**	**Max.**	**Unit**
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	52	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady-State	R_{thJF}	30	40	

Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 110 °C/W.

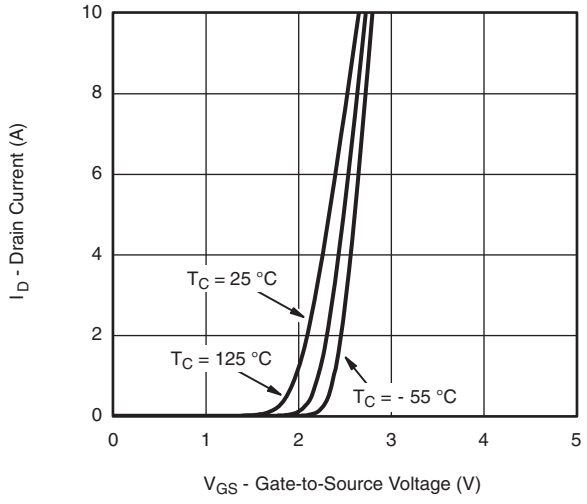
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		3.0		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 µA		- 5.2		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D= 250 µA	1.2		2.5	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, TJ = 55 °C			10	
On -State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 8 A		0.016		Ω
		V_{GS} = 4.5 V, I_D = 5 A		0.020		
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 8 A		27		S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, I_D = 1 MHz		660		pF
Output Capacitance	C_{oss}			140		
Reverse Transfer Capacitance	C_{rss}			86		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 8 A		14.5	22	nC
		V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 8 A		7.1	11	
Gate-Source Charge	Q_{gs}			1.9		
Gate-Drain Charge	Q_{gd}			2.7		
Gate Resistance	R_g	f = 1 MHz	0.5	2.6	5.2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 3 Ω I_D ≅ 5 A, V_{GEN} = 4.5 V, R_g = 1 Ω		14	28	ns
Rise Time	t_r			45	80	
Turn-Off Delay Time	$t_{d(off)}$			18	35	
Fall Time	t_f			12	24	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 3 Ω I_D ≅ 5 A, V_{GEN} = 10 V, R_g = 1 Ω		7	14	
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			15	30	
Fall Time	t_f			7	14	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			2.8	A
Pulse Diode Forward Current[a]	I_{SM}				30	
Body Diode Voltage	V_{SD}	I_S = 2 A		0.77	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 5 A, dI/dt = 100 A/µs, T_J = 25 °C		17	34	ns
Body Diode Reverse Recovery Charge	Q_{rr}			9	18	nC
Reverse Recovery Fall Time	t_a			10		nS
Reverse Recovery Rise Time	t_b			7		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

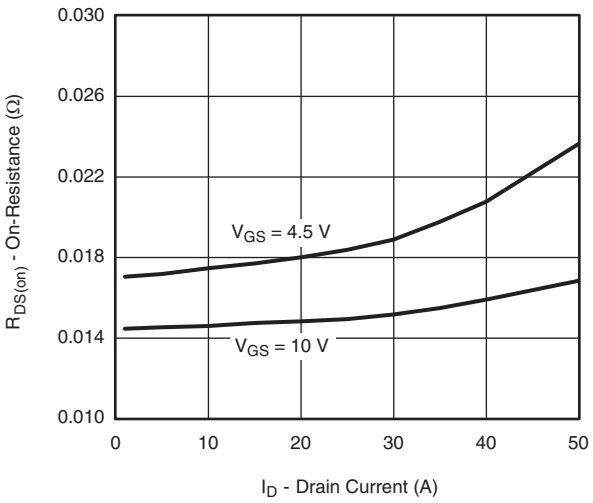
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



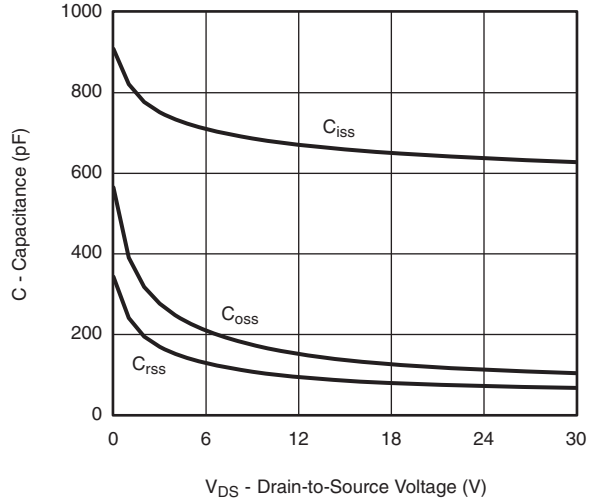
Output Characteristics



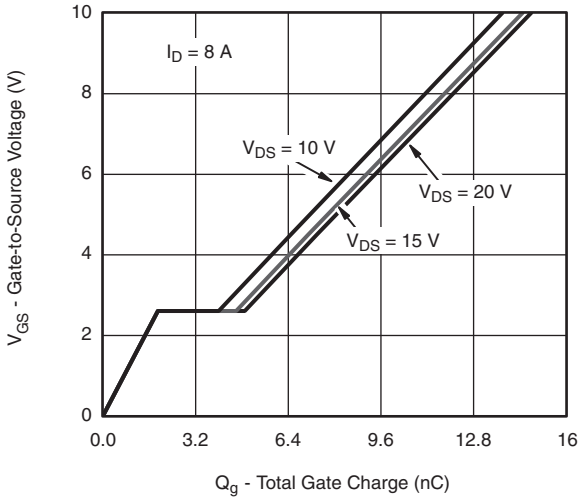
Transfer Characteristics



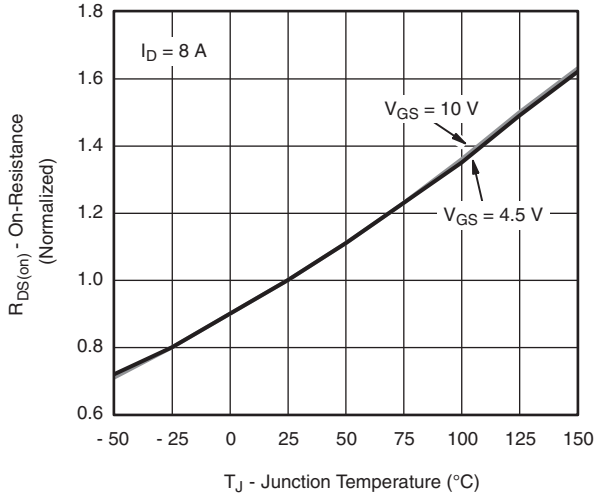
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

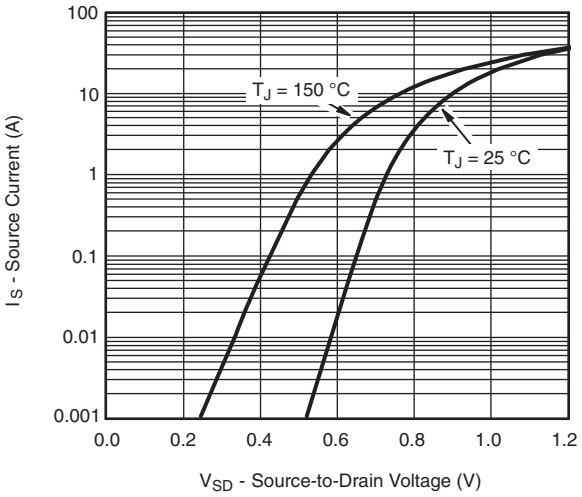


Gate Charge

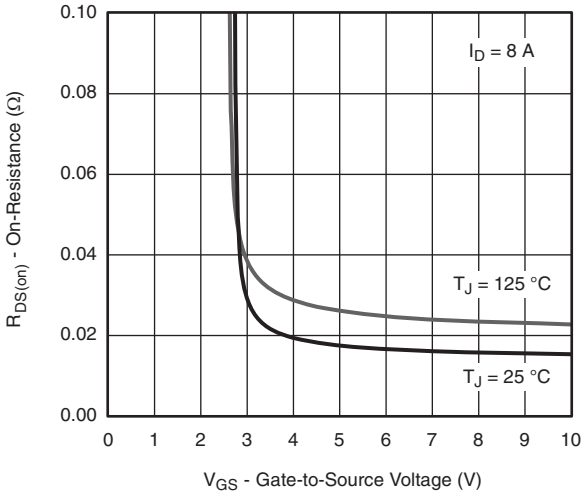


On-Resistance vs. Junction Temperature

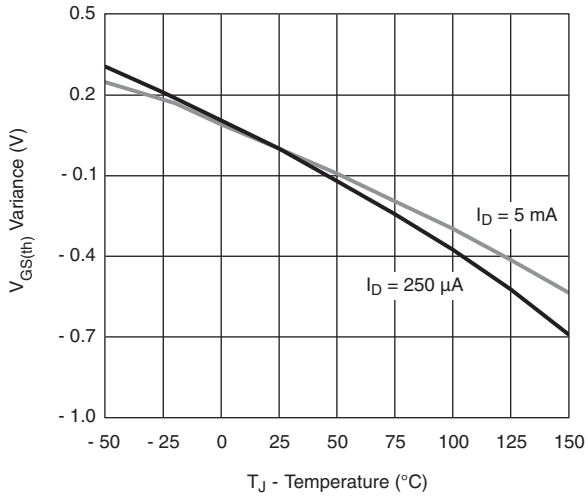
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



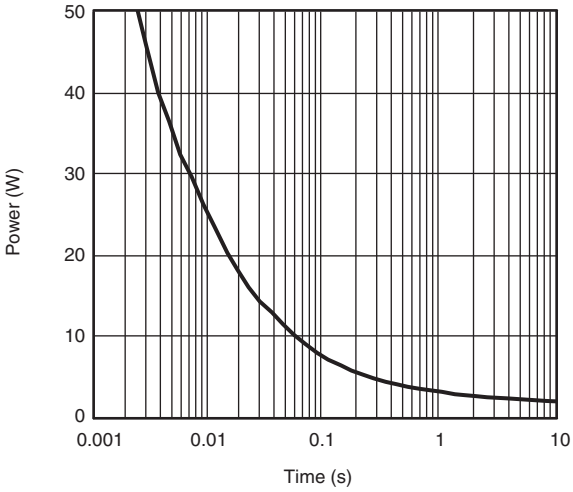
Source-Drain Diode Forward Voltage



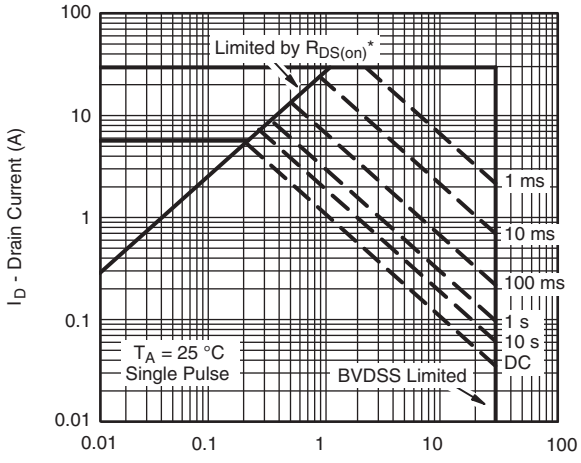
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



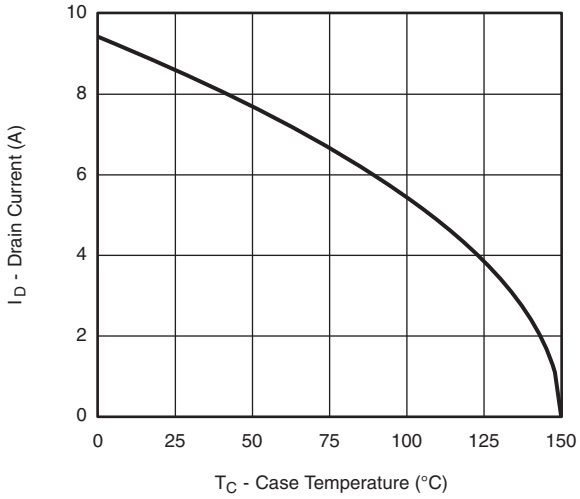
Single Pulse Power, Junction-to-Ambient



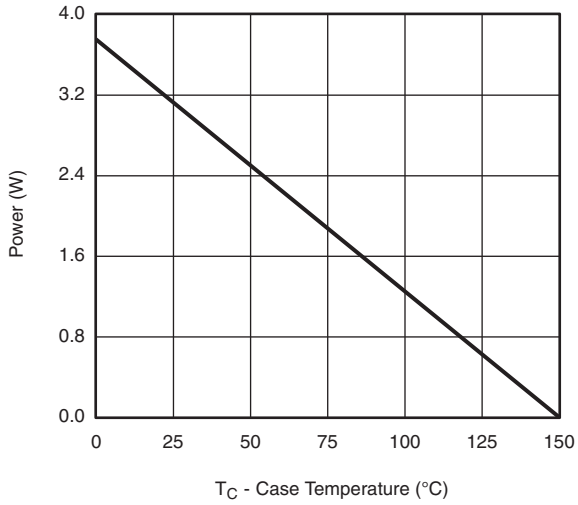
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

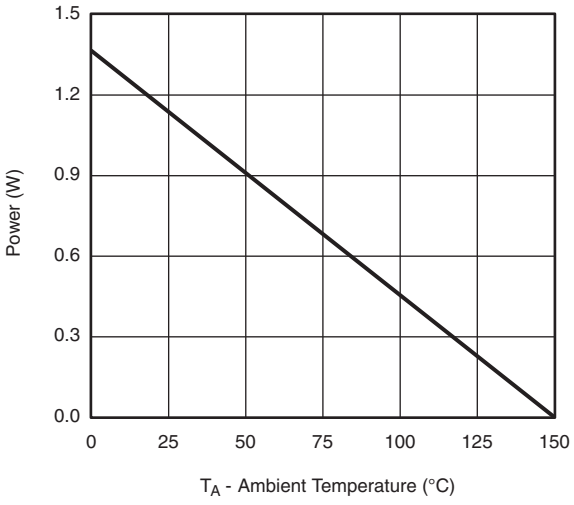
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



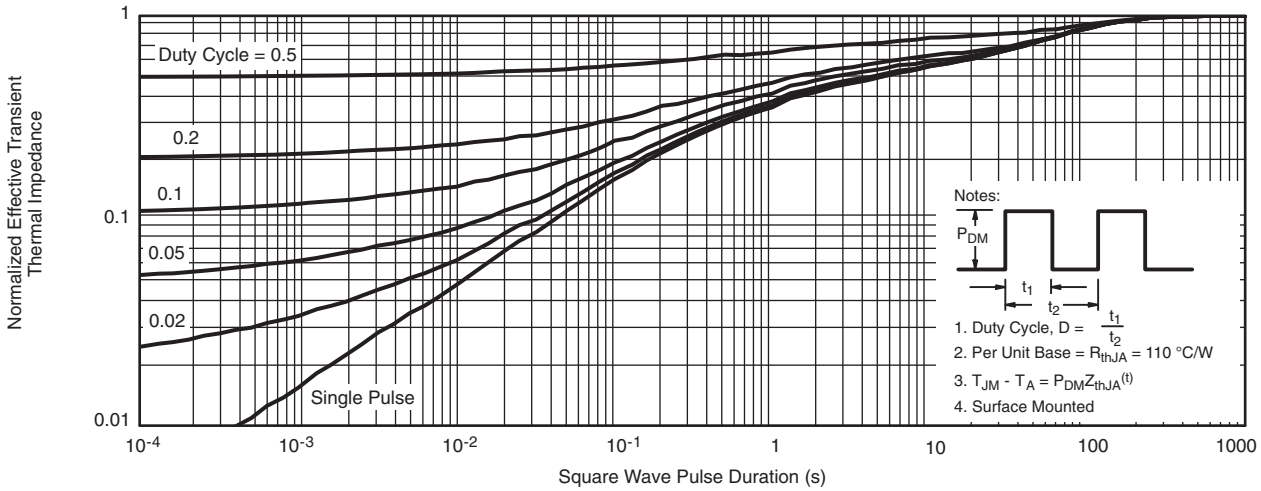
Power Derating, Junction-to-Foot



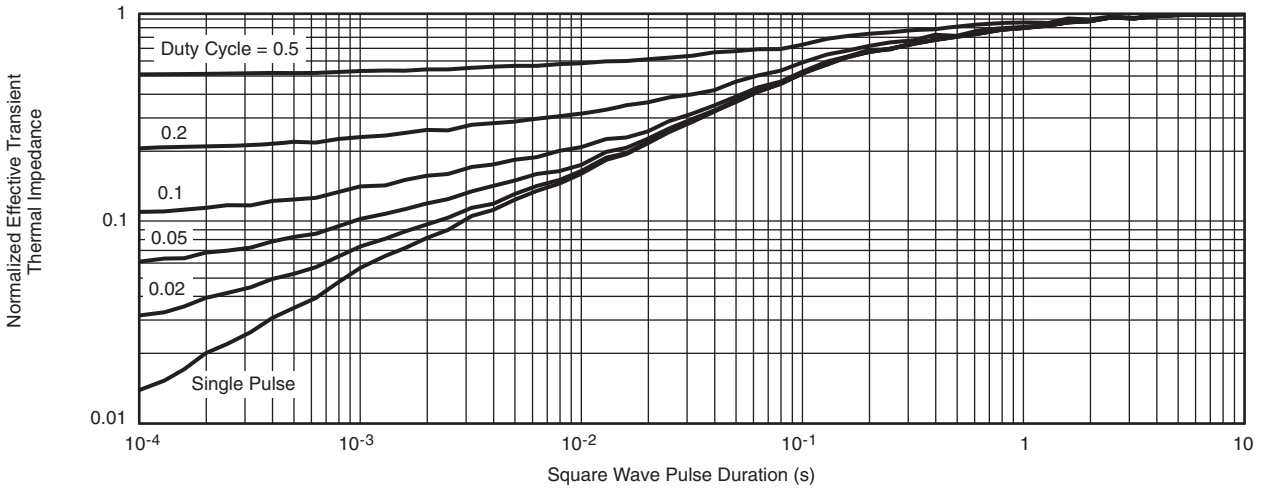
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

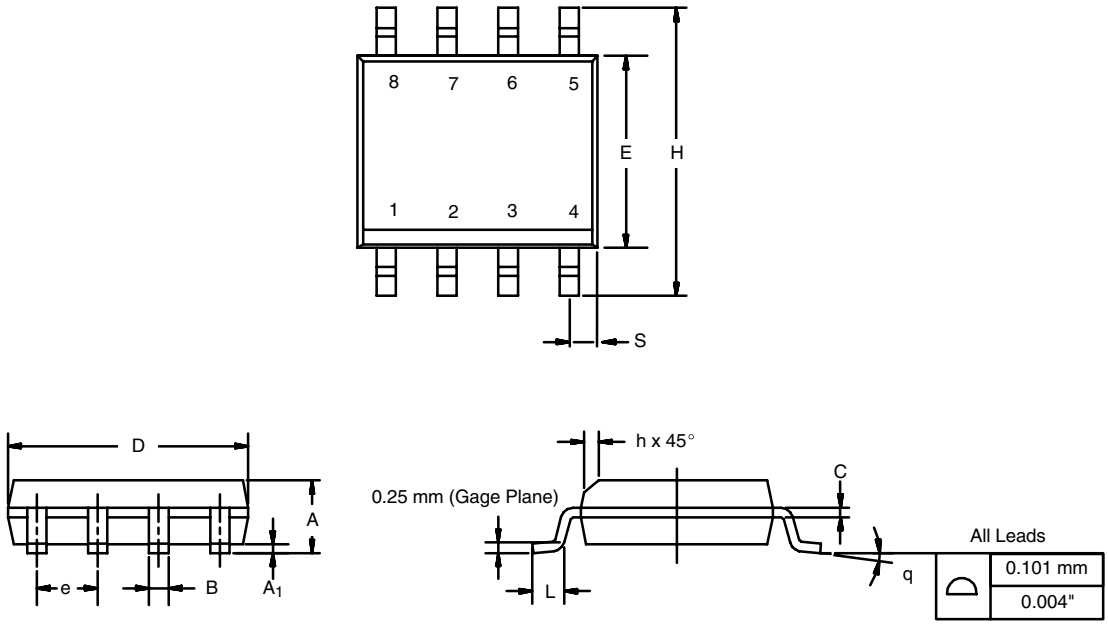


Normalized Thermal Transient Impedance, Junction-to-Ambient



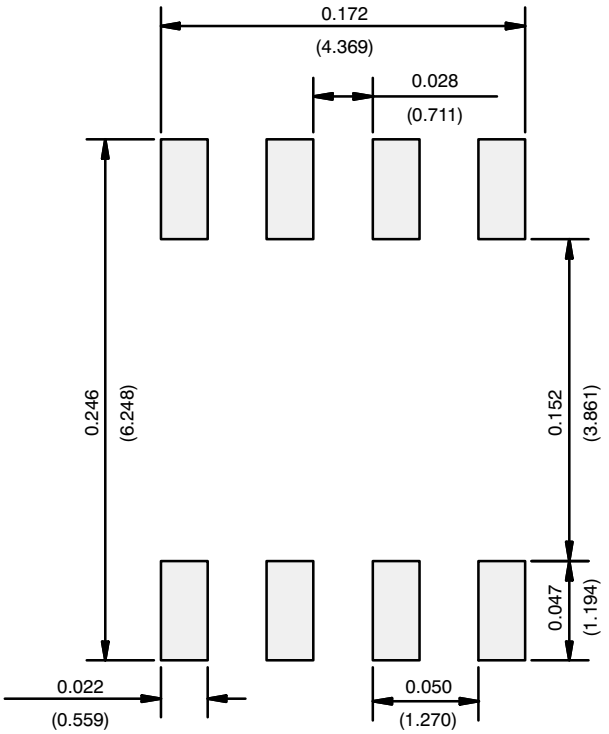
Normalized Thermal Transient Impedance, Junction-to-Foot

SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

Disclaimer

All products due to improve reliability, function or design or for other reasons, product specifications and data are subject to change without notice.

Shenzhen VBsemi Electronics Co., Ltd., branches, agents, employees, and all persons acting on its or their representatives (collectively, the "Shenzhen VBsemi"), assumes no responsibility for any errors, inaccuracies or incomplete data contained in the table or any other any disclosure of any information related to the product.(www.VBsemi.com)

Shenzhen VBsemi makes no guarantee, representation or warranty on the product for any particular purpose of any goods or continuous production. To the maximum extent permitted by applicable law on Shenzhen VBsemi relinquished: (1) any application and all liability arising out of or use of any products; (2) any and all liability, including but not limited to special, consequential damages or incidental ; (3) any and all implied warranties, including a particular purpose, non-infringement and merchantability guarantee.

Statement on certain types of applications are based on knowledge of the product is often used in a typical application of the general product VBsemi Shenzhen demand that the Shenzhen VBsemi of. Statement on whether the product is suitable for a particular application is non-binding. It is the customer's responsibility to verify specific product features in the products described in the specification is appropriate for use in a particular application. Parameter data sheets and technical specifications can be provided may vary depending on the application and performance over time. All operating parameters, including typical parameters must be made by customer's technical experts validated for each customer application. Product specifications do not expand or modify Shenzhen VBsemi purchasing terms and conditions, including but not limited to warranty herein.

Unless expressly stated in writing, Shenzhen VBsemi products are not intended for use in medical, life saving, or life sustaining applications or any other application. Wherein VBsemi product failure could lead to personal injury or death, use or sale of products used in Shenzhen VBsemi such applications using client did not express their own risk. Contact your authorized Shenzhen VBsemi people who are related to product design applications and other terms and conditions in writing.

The information provided in this document and the company's products without a license, express or implied, by estoppel or otherwise, to any intellectual property rights granted to the VBsemi act or document. Product names and trademarks referred to herein are trademarks of their respective representatives will be all.

Material Category Policy

Shenzhen VBsemi Electronics Co., Ltd., hereby certify that all of the products are determined to be RoHS compliant and meets the definition of restrictions under Directive of the European Parliament 2011/65 / EU, 2011 Nian. 6. 8 Ri Yue restrict the use of certain hazardous substances in electrical and electronic equipment (EEE) - modification, unless otherwise specified as inconsistent.(www.VBsemi.com)

Please note that some documents may still refer to Shenzhen VBsemi RoHS Directive 2002/95 / EC. We confirm that all products identified as consistent with the Directive 2002/95 / EC European Directive 2011/65 /.

Shenzhen VBsemi Electronics Co., Ltd. hereby certify that all of its products comply identified as halogen-free halogen-free standards required by the JEDEC JS709A. Please note that some Shenzhenese VBsemi documents still refer to the definition of IEC 61249-2-21, and we are sure that all products conform to confirm compliance with IEC 61249-2-21 standard level JS709A.